

Docket No.: 60188-575

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of	:	Customer Number: 20277
	:	
Takashi NISHIKAWA, et al.	:	Confirmation Number:
	:	
Serial No.: Continuation of Appl. No. 10/107,334	:	Group Art Unit:
	:	
Filed: November 07, 2003	:	Examiner:
	:	
For: DIELECTRIC FILM AND METHOD FOR FORMING THE SAME	:	

INFORMATION DISCLOSURE STATEMENT

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The references were cited by or submitted to the U.S. Patent and Trademark Office in parent application Serial No. 10/107,334, filed March 28, 2002, which is relied upon for an

Serial No.: Continuation of Appl. No.

earlier filing date under 35 USC 120. Thus, copies of these references are not attached. 37 CFR 1.98(d).

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 60188-575		SERIAL NO. Continuation of Appl. No. 10/107,334	
				APPLICANT Takashi NISHIKAWA, et al.			
				FILING DATE November 07, 2003		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		US	6,469,334	10/2002	Arita et al.		
		US	6,265,353	07/2001	Kinder et al.		
		US	5,514,484	05/1996	Nashimoto		
		US	6,214,712	04/2001	Norton		
		US	4,479,297	10/30/1984	Mizutani et al.		
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FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number + -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		JP 57-211267	12/25/1982	Toshiba Corp			
		JP 8-162614	06/21/1994	TDK Corp.			
		JP 10-231196	09/02/1998	Sony Corp.			
		JP 10-199999	07/31/1998	Asahi Chem Ind. Co Ltd.			
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		JP 2000-344599	12/12/2000	Sony Corp.			
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
		I. SAKAI et al., "Preparation and Characterization of PZT Thin Films on CeO ₂ (111)/Si(111) Structures", Jpn. J. Appl. Phys., Vol. 35, Part 1, No. 9B, pages 4987-4990, September 1996.					
		T. INOUE et al., "Intermediate Amorphous Layer Formation Mechanism at the Interface of Epitaxial CeO ₂ Layers and Si Substrates", Jpn. J. Appl. Phys., Vol. 32, Part 1, No. 4, pages 1765-1767, April 1993.					
		S. YAEHASHI et al., "Epitaxial Growth of CeO ₂ Films on Si(111) by Sputtering", Jpn. J. Appl. Phys., Vol. 33, Part 1, No. 1A, pages 270-274, January 1994.					
		H. KOINUMA et al., "Ceramic layer epitaxy by pulsed layer deposition in an ultrahigh vacuum system", Appl. Phys. Lett., 58(18), pages 2027-2029, 6 May 1991.					
		T. INOUE et al., "Texture Structure Analysis and Crystalline Quality Improvement of CeO ₂ (110) Layers Grown on Si(100) Substrates", Jpn. J. Appl. Phys., Vol. 31, Part 2, No. 12B, pages L1736-L1739, 15 December 1992.					
		M. YOSHIMOTO et al., "In Situ RHEED Observation of CeO ₂ Film Growth on Si by Laser Ablation Deposition in Ultrahigh-Vacuum", Japanese Journal of Applied Physics, Vol. 29, No. 7, pages L1199-L1202, July 1990.					
EXAMINER				DATE CONSIDERED			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.